

ABSTRACT OF THE DISCLOSURE

There are provided a step of forming an insulating film over a semiconductor substrate, a step of exciting a plasma of a gas having a molecular structure in which hydrogen and nitrogen are bonded and then irradiating the plasma onto the insulating film, a step of forming a self-orientation layer made of substance having a self-orientation characteristic on the insulating film, and a step of forming a first conductive film made of conductive substance having the self-orientation characteristic on the self-orientation layer.